

METHOD OF MANUFACTURING A FLASH MEMORY CELL

ABSTRACT OF THE DISCLOSURE

5 The present invention relates to a method of manufacturing a flash
memory cell. A tunnel oxide film is formed before a trench is formed and
an exposed portion is then etched by a given thickness. Therefore, a
phenomenon that the corner of the trench is thinly formed by a sidewall
oxidization process is prevented and an active region of a desired critical
10 dimension can be secured.